

### General Description

The WSD2075DN is the highest performance trench Dual P-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD2075DN meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

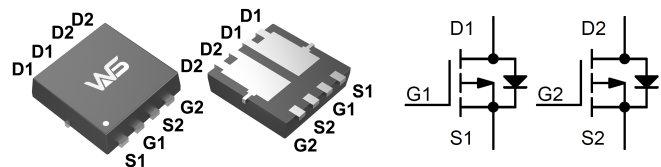
### Product Summary

BVDSS	RDSON	ID
-20V	9.5mΩ	-36A

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

### DFN3x3A-8\_EP Pin Configuration



### Absolute Maximum Ratings @TA=25°C unless otherwise noted

Symbol	Parameter	Ratings	Unit	
V <sub>bss</sub>	Drain-Source Voltage	-20	V	
V <sub>GSS</sub>	Gate-Source Voltage	±12	V	
I <sub>D</sub>	Drain Current (Continuous) *AC	T <sub>C</sub> =25°C	-36	A
		T <sub>C</sub> =100°C	-23	A
I <sub>DM</sub>	Drain Current (Pulse) *B	-108	A	
P <sub>D</sub>	Power Dissipation	T <sub>C</sub> =25°C	23	W
T <sub>J</sub> /T <sub>STG</sub>	Operating Temperature/ Storage Temperature	-55~150	°C	
R <sub>thJC</sub>	Maximum Junction-to-Ambient	5.4	°C/W	

**Electrical Characteristics @ $T_A=25^{\circ}\text{C}$  unless otherwise noted**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	-20	---	---	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -20V, V_{GS} = 0V$	---	---	-1	$\mu A$
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{DS} = 250\mu A$	-0.4	-0.8	-1.2	V
$I_{GSS}$	Gate Leakage Current	$V_{GS} = \pm 12V, V_{DS} = 0V$	---	---	$\pm 100$	nA
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS} = -10V, I_D = -6A$	---	9.5	12	m $\Omega$
		$V_{GS} = -4.5V, I_D = -6A$	---	11	14	m $\Omega$
		$V_{GS} = -2.5V, I_D = -4A$	---	14	18	m $\Omega$
$V_{SD}$	Diode Forward Voltage	$I_{SD} = -1A, V_{GS} = 0V$	---	-0.73	-1.2	V
$I_S$	Diode Forward Current *AC	$T_C = 25^{\circ}\text{C}$	---	---	-19	A
<b>Switching</b>						
$Q_g$	Total Gate Charge	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -9.5A$	---	28	---	nC
$Q_{gs}$	Gate-Source Charge		---	3.5	---	nC
$Q_{gd}$	Gate-Drain Charge		---	5.6	---	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = -10V, R_L = 1.3\Omega, I_D \cong -7.6A, V_{GEN} = -4.5V, R_g = 1\Omega$	---	30	---	ns
$t_r$	Turn-on Rise Time		---	54	---	ns
$t_{d(off)}$	Turn-off Delay Time		---	135	---	ns
$t_f$	Turn-Off Fall Time		---	63	---	ns
<b>Dynamic</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -10V, V_{GS} = 0V, f = 1\text{ MHz}$	---	2565	---	pF
$C_{oss}$	Output Capacitance		---	260	---	pF
$C_{rss}$	Reverse Transfer Capacitance		---	240	---	pF

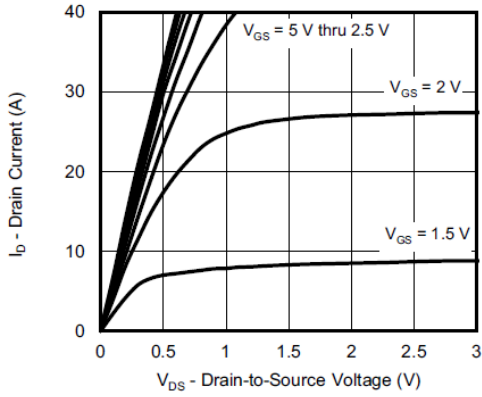
A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ .

The value in any given application depends on the user's specific board design.

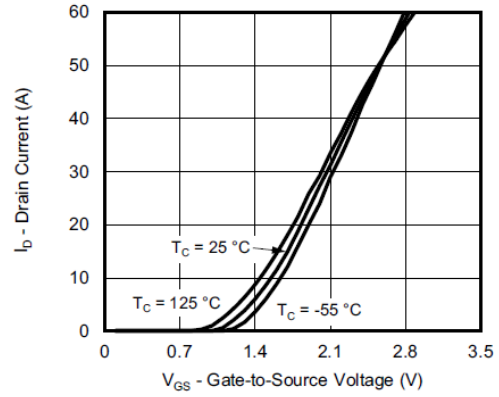
B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the  $t \leq 10s$  junction to ambient thermal resistance rating, Wire Bond Limited 10A.

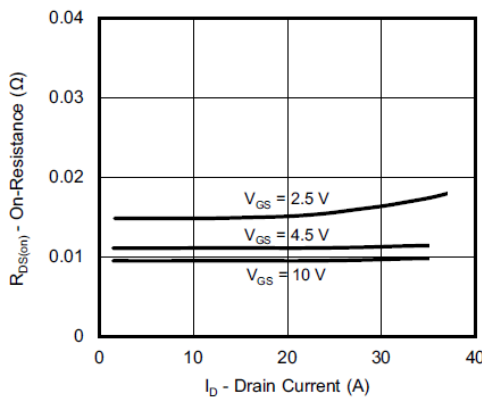
**Typical Characteristics**



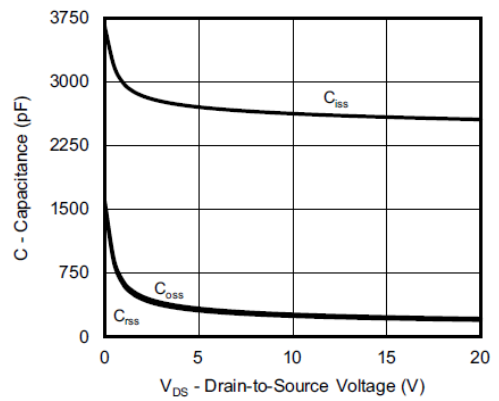
**Output Characteristics**



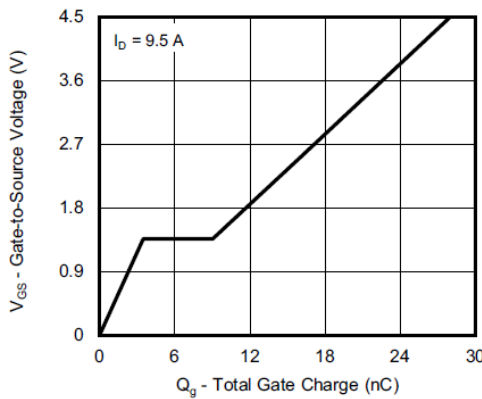
**Transfer Characteristics**



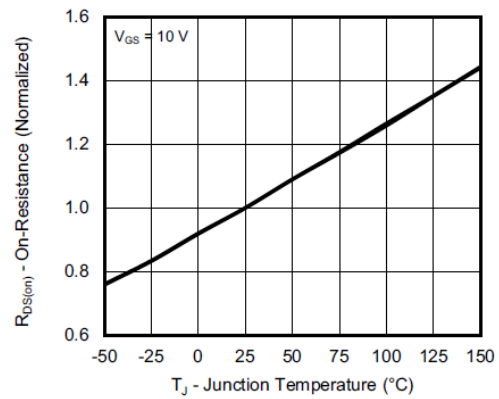
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**

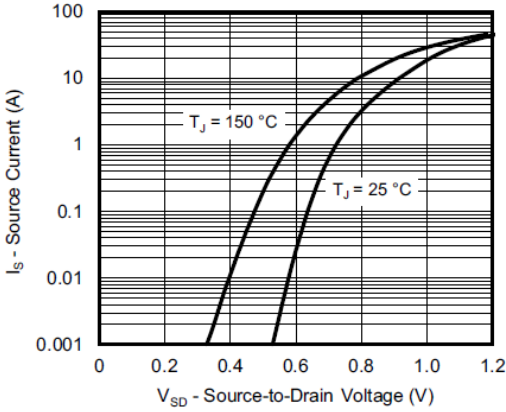


**Gate Charge**

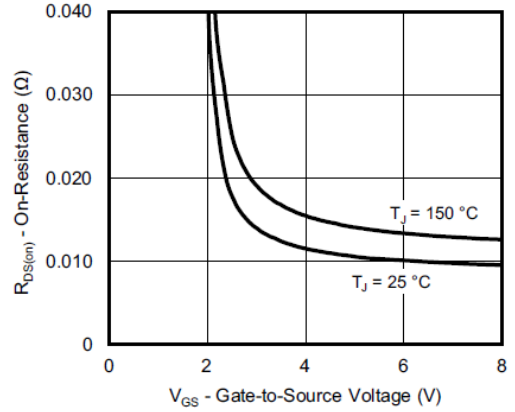


**On-Resistance vs. Junction Temperature**

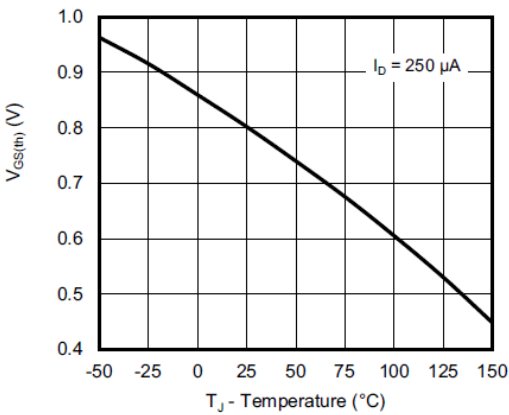
**Typical Characteristics**



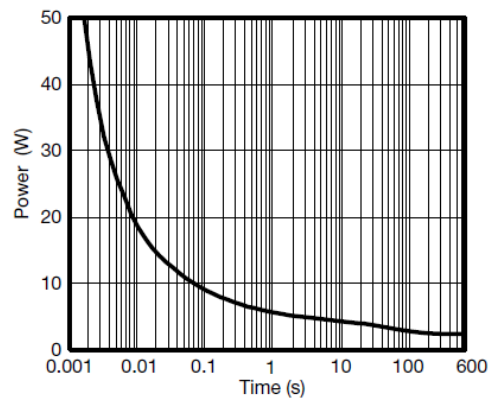
Source-Drain Diode Forward Voltage



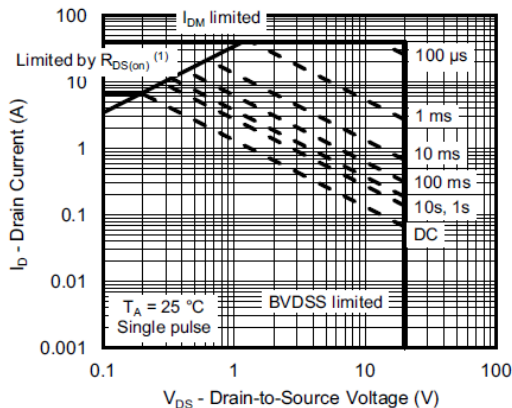
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

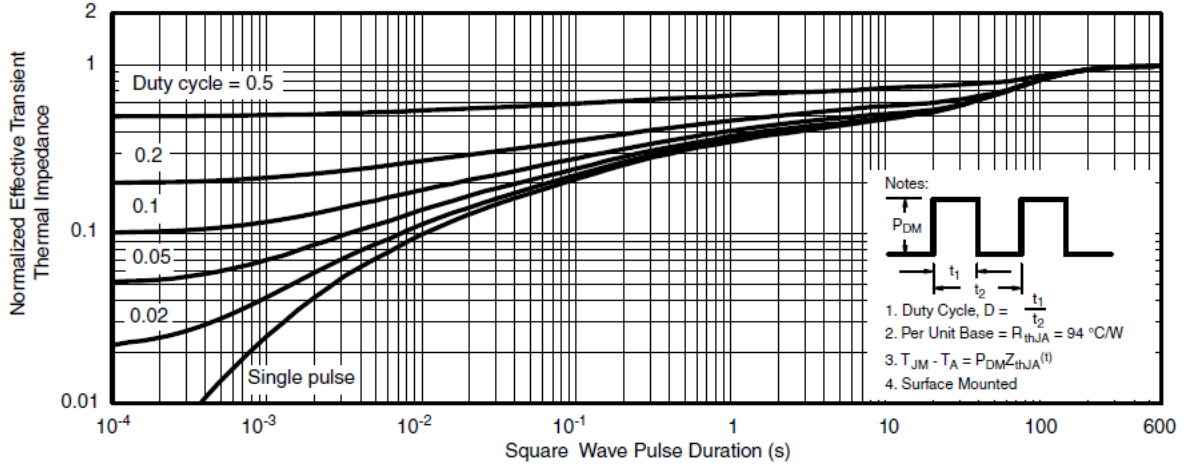


Single Pulse Power, Junction-to-Ambient

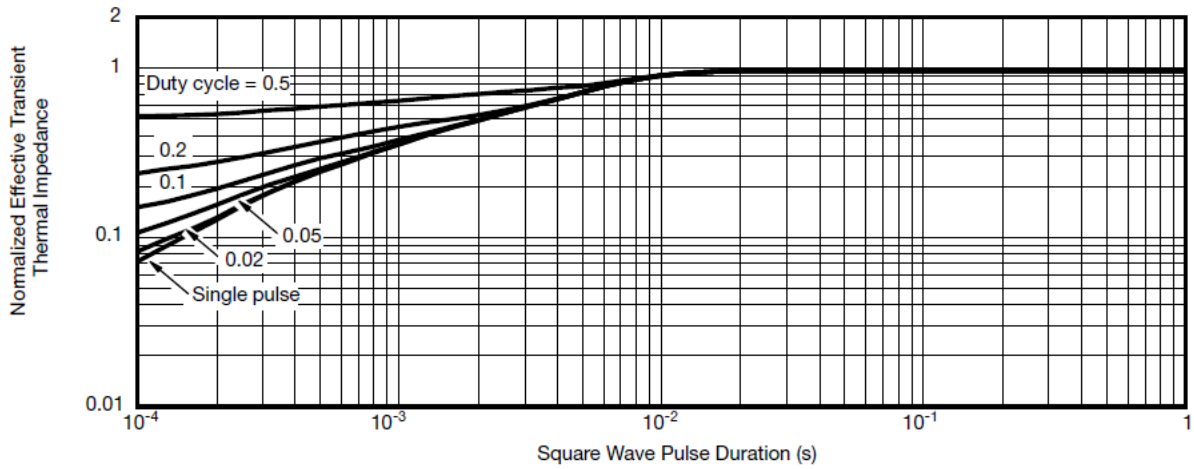


Safe Operating Area, Junction-to-Ambient

**Typical Characteristics**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Case**



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